

APPLICATION NO. 10/811056

February 23, 2005

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1. (Currently Amended) A semiconductor device comprising:
a first insulating film on a silicon substrate; and
a second insulating film on said first insulating film, wherein
said first insulating film is a silicon oxide film having a film thickness of not exceeding 1 nm or less and a suboxide content of not exceeding 30% or less; and
said second insulating film is a high dielectric constant insulating film.
2. (Currently Amended) The semiconductor device according to claim 1, wherein
said high dielectric constant insulating film is selected from the group consisting of a metal oxide film or and a metal silicate film.
3. (Currently Amended) The semiconductor device according to claim 2, wherein
said metal oxide film is an oxide film of including at least one metal selected from a the
group consisting of hafnium, zirconium, lanthanum, and yttrium.
4. (Currently Amended) The semiconductor device according to claim 2, wherein
said metal silicate film is a silicate film of including at least one metal selected from a the
group consisting of hafnium, zirconium, lanthanum, yttrium, and aluminum.
5. (Original) The semiconductor device according to claim 4, wherein said metal
silicate film contains nitrogen.
6. (Currently Amended) A semiconductor device comprising:
a first insulating film on a silicon substrate; and
a second insulating film on said first insulating film, wherein
said first insulating film is a silicon oxynitride film having a film thickness of not exceeding 1 nm or less and a suboxide content of not exceeding 30% or less; and
said second insulating film is a high dielectric constant insulating film.
7. (Currently Amended) The semiconductor device according to claim 6, wherein
said high dielectric constant insulating film is selected from the group consisting of a metal oxide film or and a metal silicate film.

8. (Currently Amended) The semiconductor device according to claim 7, wherein said metal oxide film is an oxide film ~~of~~ including at least one metal selected from ~~a~~ the group consisting of hafnium, zirconium, lanthanum, and yttrium.

9. (Currently Amended) The semiconductor device according to claim 7, wherein said metal silicate film is a silicate film ~~of~~ including at least one metal selected from ~~a~~ the group consisting of hafnium, zirconium, lanthanum, yttrium, and aluminum.

10. (Original) The semiconductor device according to claim 9, wherein said metal silicate film contains nitrogen.

11. (Currently Amended) A semiconductor device comprising:
a first insulating film on a silicon substrate; and
a second insulating film on said first insulating film, wherein
said first insulating film is a silicon nitride film having a ~~film~~ thickness ~~of~~ not
exceeding 1 nm ~~or less~~ and an oxygen content ~~of less than~~ not exceeding 0.1 atom%; and
said second insulating film is a high dielectric constant insulating film.

CLAIMS 12-23 (CANCELLED)